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CSD16407Q5

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# N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16407Q5

#### **FEATURES**

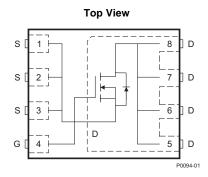
- · Ultralow Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- SON 5-mm × 6-mm Plastic Package

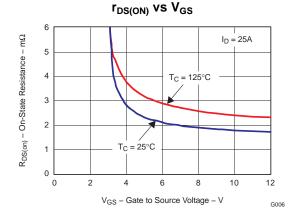
#### **APPLICATIONS**

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

#### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





#### **PRODUCT SUMMARY**

V <sub>DS</sub>	Drain-to0source voltage	25		V
$Q_g$	Gate charge, total (4.5 V)	13.3		nC
$Q_{gd}$	Gate charge, gate-to-drain	3.5		nC
R <sub>DS(on)</sub>	Drain-to-source on-resistance	V <sub>GS</sub> = 4.5 V	2.5	mΩ
		V <sub>GS</sub> = 10 V	1.8	mΩ
V <sub>GS(th)</sub>	Threshold voltage	1.6		V

#### ORDERING INFORMATION

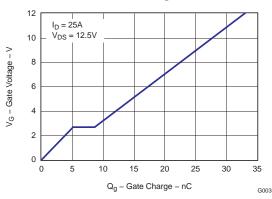
ſ	Device	Package	Media	Qty	Ship
ĺ	CSD16407Q5	SON 5 × 6 plastic package	13-inch reel	2500	Tape and reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain-to-source voltage	25	V
V <sub>GS</sub>	Gate-to-source voltage	+16 / -12	V
	Continuous drain current, T <sub>C</sub> = 25°C	100	Α
I <sub>D</sub>	Continuous drain current <sup>(1)</sup>	31	Α
I <sub>DM</sub>	Pulsed drain current, T <sub>A</sub> = 25°C <sup>(2)</sup>	200	Α
$P_D$	Power dissipation <sup>(1)</sup>	3.1	W
T <sub>J</sub> , T <sub>STG</sub>	Operating junction and storage temperature range	-55 to 150	°C
E <sub>AS</sub>	Avalanche energy, single pulse I <sub>D</sub> = 66A, L = 0.1 mH, R <sub>G</sub> = 25 $\Omega$	218	mJ

- (1)  $R_{\theta,JA} = 40^{\circ}\text{C/W}$  on 1 in<sup>2</sup> (6.45 cm<sup>2</sup>) Cu [2 oz. (0.071 mm thick)] on 0.060-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300 μs, duty cycle ≤2%

#### **Gate Charge**



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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#### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics				*	
BV <sub>DSS</sub>	Drain-to-source voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	25			V
I <sub>DSS</sub>	Drain-to-source leakage current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 20 V			1	μΑ
I <sub>GSS</sub>	Gate-to-source leakage current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 16 V to -12 V			100	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.3	1.6	1.9	V
_	Drain to course on registeres	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 25 A		2.5	3.3	mΩ
r <sub>DS(on)</sub>	Drain-to-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A		1.8	2.4	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 25 A		111		S
Dynamic	Characteristics				*	
C <sub>ISS</sub>	Input capacitance			2040	2660	pF
Coss	Output capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 12.5 V, f = 1 MHz		1600	2080	pF
C <sub>RSS</sub>	Reverse transfer capacitance			115	160	pF
R <sub>g</sub>	Series gate resistance			1.2	2.4	Ω
Qg	Gate charge total (4.5 V)			13.3	18	nC
Q <sub>gd</sub>	Gate charge, gate-to-drain	V 40.5 V 1 05.4		3.5		nC
Q <sub>gs</sub>	Gate charge, gate-to-source	V <sub>DS</sub> = 12.5 V, I <sub>D</sub> = 25 A		5.3		nC
Qg(th)	Gate charge at Vth			3.1		nC
Q <sub>OSS</sub>	Output charge	V <sub>DS</sub> = 13.5 V, V <sub>GS</sub> = 0 V		33		nC
t <sub>d(on)</sub>	Turnon delay time			11.9		ns
t <sub>r</sub>	Rise time	V <sub>DS</sub> = 12.5 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 25 A		18.4		ns
t <sub>d(off)</sub>	Turnoff delay time	$R_G = 2 \Omega$		16		ns
t <sub>f</sub>	Fall time			9		ns
Diode C	haracteristics				,	
V <sub>SD</sub>	Diode forward voltage	I <sub>S</sub> = 25 A, V <sub>GS</sub> = 0 V		0.8	1	V
Q <sub>rr</sub>	Reverse recovery charge	$V_{DD} = 13.5 \text{ V}, I_F = 25 \text{ A}, di/dt = 300 \text{ A/}\mu\text{s}$		41		nC
t <sub>rr</sub>	Reverse recovery time	V <sub>DD</sub> = 13.5 V, I <sub>F</sub> = 25 A, di/dt = 300 A/μs		34		ns

#### THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal resistance, junction-to-case <sup>(1)</sup>			1.1	°C/W
R <sub>θJA</sub>	Thermal resistance, junction-to-ambient (1) (2)			51	°C/W

R<sub>θJC</sub> is determined with the device mounted on a 1-inch (2.54-cm) square 2-oz (0.071-mm thick). Cu pad on a 1.5-inch (3.81-cn) × 1.5-inch (3.81-cm) × 0.060-inch (1.52-mm) thick FR4 board. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.

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<sup>(2)</sup> Device mounted on FR4 material with 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-oz. (0.071-mm thick) Cu.

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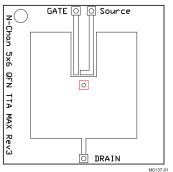
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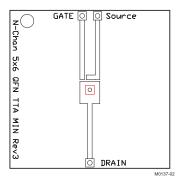
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Max  $R_{\theta JA} = 50^{\circ} C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 121^{\circ} C/W$  when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

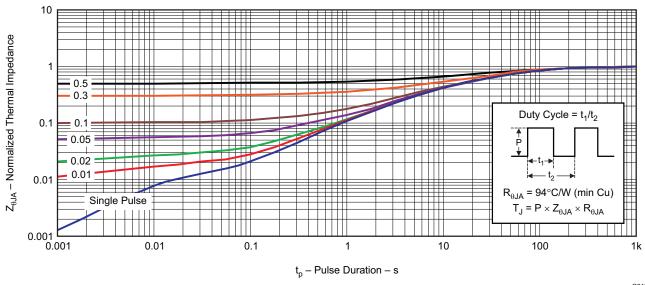


Figure 1. Transient Thermal Impedance

G012

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# **TYPICAL MOSFET CHARACTERISTICS (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)

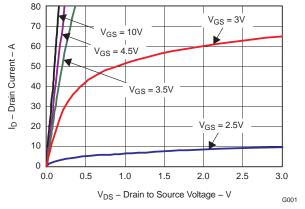


Figure 2. Saturation Characteristics

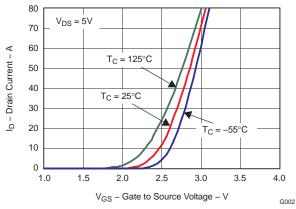


Figure 3. Transfer Characteristics

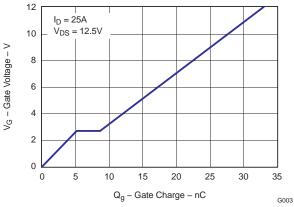


Figure 4. Gate Charge

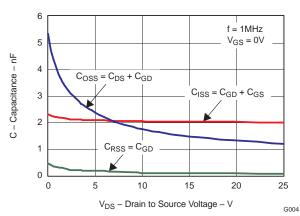


Figure 5. Capacitance

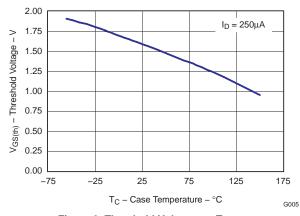


Figure 6. Threshold Voltage vs. Temperature

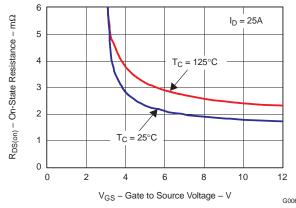


Figure 7. On Resistance vs. Gate Voltage



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### **TYPICAL MOSFET CHARACTERISTICS (continued)**

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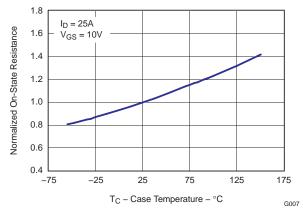


Figure 8. On Resistance vs. Temperature

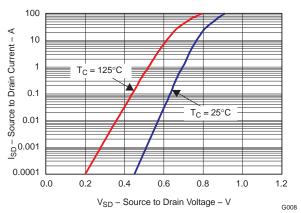


Figure 9. Typical Diode Forward Voltage

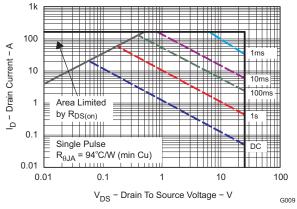


Figure 10. Maximum Safe Operating Area

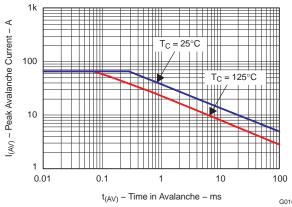


Figure 11. Single Pulse Unclamped Inductive Switching

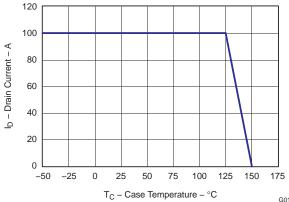


Figure 12. Maximum Drain Current vs. Temperature

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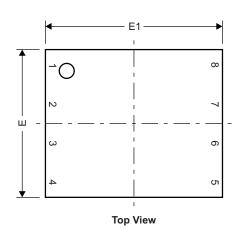


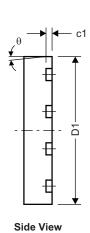
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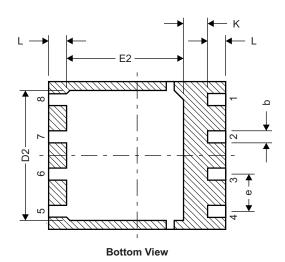
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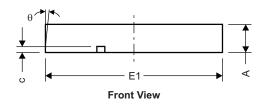
### **MECHANICAL DATA**

# **Q5 Package Dimensions**









M0140-01

DIM	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
е	1.27	TYP	0.050	
L	0.510	0.710	0.020	0.028
θ	0.00	-	_	_
К	0.760	-	0.030	_

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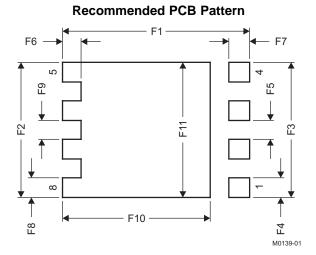
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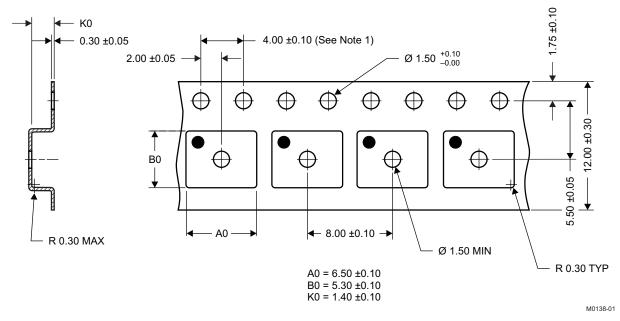
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DIM	MILLIM	IETERS	INC	HES
DIW	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.2440	0.248
F2	4.460	4.560	0.1760	0.180
F3	4.460	4.560	0.1760	0.180
F4	0.650	0.700	0.0260	0.028
F5	0.620	0.670	0.0240	0.026
F6	0.630	0.680	0.0250	0.027
F7	0.70	0.800	0.0380	0.031
F8	0.650	0.700	0.0260	0.028
F9	0.620	0.670	0.0240	0.026
F10	4.900	5.000	0.1930	0.197
F11	4.460	4.560	0.1760	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

#### **Q5** Tape and Reel Information



#### Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm IN 100 mm, noncumulative over 250 mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. Thickness: 0.30 ±0.05 mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



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#### **REVISION HISTORY**

CI	hanges from Revision Original (August 2009) to Revision A	Page
•	Deleted environmental bullets from features list	
•	Deleted package marking at end of data sheet	

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PACKAGE OPTION ADDENDUM

7-Jan-2016

#### **PACKAGING INFORMATION**

Orderable Device Lead/Ball Finish Status Package Type Package Pins Package Eco Plan MSL Peak Temp Op Temp (°C) Device Marking Samples Qty Drawing (1) (2) (6) (3) CSD16407Q5 ACTIVE VSON-CLIP 2500 Pb-Free (RoHS CU SN Level-1-260C-UNLIM CSD16407 DQH 8 -55 to 150 Samples Exempt)

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Tl's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device
- (6) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width

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